

NPN Silicon Epitaxial Planar Transistor

S

9011

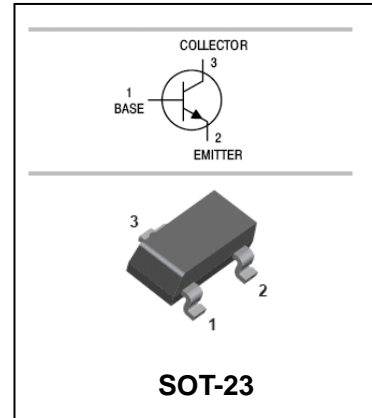
FEATURES

- Collector Current.($I_C=30\text{mA}$)
- Power dissipation.($P_C=200\text{mW}$)



APPLICATIONS

- AM converter, AM/FM if amplifier general purpose transistor.



ORDERING INFORMATION

Type No.	Marking	Package Code
S 9011	1 T	S OT-23

MAXIMUM RATING @ $T_a=25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	50 V	
V_{CEO}	Collector-Emitter Voltage	30 V	
V_{EBO}	Emitter-Base Voltage	5 V	
I_C	Collector Current -Continuous	30 mA	
P_C	Collector Dissipation	200 mW	
T_j, T_{stg}	Junction and Storage Temperature	-55~150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS @ $T_a=25^\circ\text{C}$ unless otherwise specified

Parameter S	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu\text{A}, I_E=0$ 50			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=0.1\text{mA}, I_B=0$ 30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu\text{A}, I_C=0$	5		V
Collector cut-off current	I_{CBO}	$V_{CB}=50\text{V}, I_E=0$		0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=5\text{V}, I_C=0$		0.1	μA
DC current gain	h_{FE}	$V_{CE}=5\text{V}, I_C=1\text{mA}$ 28		198	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=10\text{mA}, I_B=1\text{mA}$		0.3	V
Transition frequency	f_T	$V_{CE}=5\text{V}, I_C=1\text{mA}$	150		MHz
Output capacitance	C_{ob}	$V_{CB}=10\text{V}, I_E=0, f=1\text{MHz}$		4	pF

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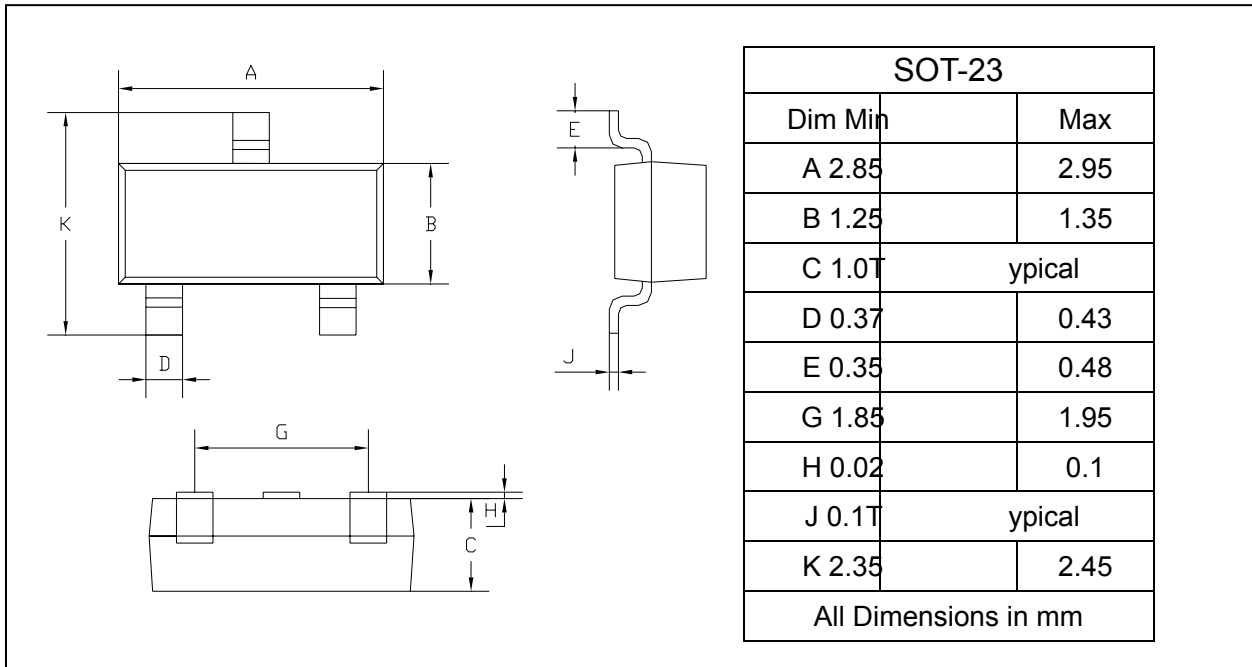
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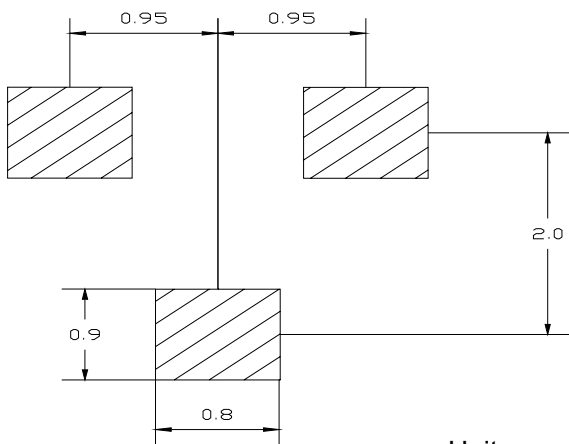
PACKAGE OUTLINE

Plastic surface mounted package

SOT -23



SOLDERING FOOTPRINT



Unit : mm

PACKAGE INFORMATION

Device	Package	Shipping
S9011	SOT-23	3000/Tape&Reel